

ABSTRACT OF THE DISCLOSURE

A nonvolatile ferroelectric memory device and a method for fabricating the same are provided that increase a process margin and simplify process steps. In addition, a number of masks is reduced to save the cost and at the same time minimize or reduce a layout area. The nonvolatile ferroelectric memory device can include first and second split wordlines formed along a first direction on a substrate at prescribed intervals, a first electrode of a first ferroelectric capacitor on the second split wordline and a first electrode of a second ferroelectric capacitor on the first split wordline; first and second ferroelectric layers respectively on surfaces of the first electrodes of the first and second ferroelectric capacitors, and second electrodes of the first and second ferroelectric capacitors, respectively, on surfaces of the first and second ferroelectric layers. A first conductive layer connects the second electrode of the first ferroelectric capacitor with the substrate at one side of the second split wordline, and a second conductive layer connects the second electrode of the second ferroelectric capacitor with the substrate at one side of the first split wordline. First and second bitlines are coupled with the substrate at another sides of the respective split wordlines.